

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Currently Amended) A susceptor in which a semiconductor substrate is supported approximately horizontally in a pocket when performing a vapor phase growth of a single crystal thin film on a front surface of the semiconductor substrate, and in which the pocket comprises an outer peripheral pocket portion to support the semiconductor substrate and a central side pocket portion which is formed inside the outer peripheral side pocket portion to be concave from the outer peripheral side pocket portion,

wherein the outer peripheral side pocket portion comprises a substrate supporting surface which is inclined with respect to a horizontal surface to be lowered toward a central side from an outer peripheral side of the pocket, and a region of the substrate supporting surface excluding at least an inner peripheral edge supports a portion of a rear surface of the semiconductor substrate which is inside an outer peripheral edge of the semiconductor-substrate-substrate,

wherein the pocket is for a silicon single crystal substrate of 300mm in diameter, and the substrate supporting surface is inclined at an angle of more than 0 degree and not more than 1 degree with respect to the horizontal.

7. (Canceled)

8. (Currently Amended) The susceptor of claim 6, wherein the substrate supporting surface is inclined ~~with respect to the horizontal surface~~ at an angle equal to an angle which is made by the horizontal surface and a tangent to the semiconductor substrate at a contact of the substrate supporting surface and the semiconductor substrate in an imaginary plane including ~~an central~~ a central axis of the pocket.

9. (Currently Amended) The susceptor of claim 7, wherein the substrate supporting surface is inclined ~~with respect to the horizontal surface~~ at an angle equal to an angle which is made by the horizontal surface and a tangent to the semiconductor substrate at a contact of the substrate supporting surface and the semiconductor substrate in an imaginary plane including ~~an central~~ a central axis of the pocket.

10. (Previously Presented) The susceptor of claim 6, wherein the central side pocket portion is concave to have a depth so as not to contact a rear surface of the semiconductor substrate.

11. (Cancelled)

12. (Previously Presented) The susceptor of claim 8, wherein the central side pocket portion is concave to have a depth so as not to contact a rear surface of the semiconductor substrate.

13. (Previously Presented) The susceptor of claim 9, wherein the central side pocket portion is concave to have a depth so as not to contact a rear surface of the semiconductor substrate.

14. (Currently Amended) A vapor phase growth apparatus comprising:
——— the susceptor of claim 6.

15. (Cancelled)

16. (Currently Amended) A vapor phase growth apparatus comprising:
——— the susceptor of claim 8.

17. (Currently Amended) A vapor phase growth apparatus comprising:
——— the susceptor of claim 9.

18. (Currently Amended) A vapor phase growth apparatus comprising:
——— the susceptor of claim 10.

19. (Cancelled)

20. (Currently Amended) A vapor phase growth apparatus comprising:

_____the susceptor of claim 12.

21. (Currently Amended) A vapor phase growth apparatus comprising:

_____the susceptor of claim 13.